

## HMHL065N185C

### 650-V Cascode GaN HEMT

#### Description

These miniature surface mount GaN HEMT utilize a GaN transistor technology to provide low  $R_{DS(on)}$  and using the Cascode in the DFN package to realize the normal-off high electron mobility transistor.

Also provides high breakdown voltage, high current and high operating speed which is suitable for high power applications.

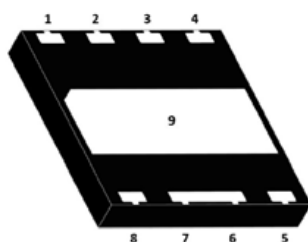
#### Features

- Gate drive voltage compatibility (-20V to 20V)
- High operating frequency
- Low  $Q_{rr}$

#### Typical Applications

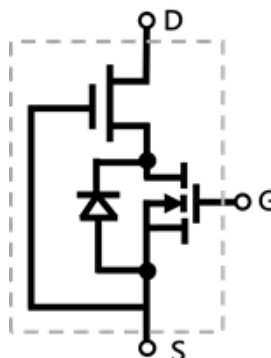
- Switch Mode Power Supplies (SMPS)
- AC-DC/ DC-DC Converters
- Motor Drives

#### Package type : DFN 8X8

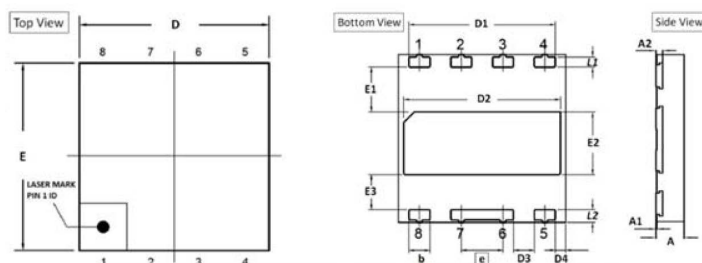


Drain: 1, 2, 3, 4  
Source: 5, 6, 7, 9  
Gate: 8

#### Graphic Symbol

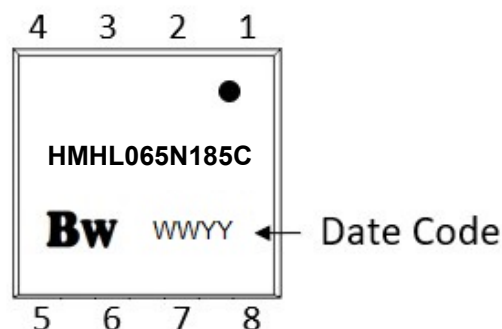


#### Package Dimension



| SYMBOL | DIMENSION(unit : mm) |      |      | SYMBOL | DIMENSION(unit : mm) |      |      |
|--------|----------------------|------|------|--------|----------------------|------|------|
|        | MIN                  | TYP  | MAX  |        | MIN                  | TYP  | MAX  |
| A      | 1.20                 | 1.25 | 1.30 | e      | 2.00 BSC             |      |      |
| A1     | --                   | 0.02 | 0.05 | E      | 7.90                 | 8.00 | 8.10 |
| A2     | 0.203 REF            |      |      | E1     | 2.00                 | 2.10 | 2.20 |
| b      | 0.95                 | 1.00 | 1.05 | E2     | 2.90                 | 3.00 | 3.10 |
| D      | 7.90                 | 8.00 | 8.10 | E3     | 1.60                 | 1.70 | 1.80 |
| D1     | 6.90                 | 7.00 | 7.10 | L1     | 0.38                 | 0.48 | 0.58 |
| D2     | 7.40                 | 7.50 | 7.60 | L2     | 0.50                 | 0.60 | 0.70 |
| D3     | 0.90                 | 1.00 | 1.10 |        |                      |      |      |
| D4     | 0.40                 | 0.50 | 0.60 |        |                      |      |      |

#### Marking



RoHS Compliant

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#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

##### Absolute Maximum Ratings

| Symbol               | Parameter                                                          | Value     | Units            |
|----------------------|--------------------------------------------------------------------|-----------|------------------|
| $V_{DS}$             | Drain-Source Voltage                                               | 650       | V                |
| $V_{(TR)DSS}$        | Transient drain to source voltage <sup>1</sup>                     | 800       | V                |
| $V_{GS}$             | Gate-Source Voltage                                                | -20 / +20 | V                |
| $I_D$                | Continuous Drain Current at $T_C = 25^\circ\text{C}$               | 12        | A                |
|                      | Continuous Drain Current at $T_C = 100^\circ\text{C}$              | 8         | A                |
| $I_{D\text{ pulse}}$ | Pulse Drain Current (Pulse width = 10 $\mu\text{s}$ ) <sup>2</sup> | 21        | A                |
| $T_J/T_{STG}$        | Operating Junction and Storage Temperature                         | -55...150 | $^\circ\text{C}$ |
| $T_{SOLD}$           | Soldering peak temperature                                         | 260       | $^\circ\text{C}$ |

#### Notes

1. In off-state, spike duty cycle  $D < 0.01$ , spike duration  $< 1\ \mu\text{s}$
2. Value is not tested to full current in production.

##### Thermal Resistance Ratings

| Symbol          | Parameter                   | Maximum | Units              |
|-----------------|-----------------------------|---------|--------------------|
| $R_{\theta JA}$ | Maximum Junction-to-Ambient | 54      | $^\circ\text{C/W}$ |
| $R_{\theta JC}$ | Maximum Junction-to-Case    | 2.8     | $^\circ\text{C/W}$ |

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### 650-V Cascode GaN HEMT

#### Static Electrical Characteristics, ( $T_J=25^\circ\text{C}$ unless otherwise specified)

| Symbol       | Parameter                         | Test Conditions                                                     | Min. | Typ. | Max.      | Units            |
|--------------|-----------------------------------|---------------------------------------------------------------------|------|------|-----------|------------------|
| $V_{GS(th)}$ | Gate Threshold Voltage            | $V_{DS}=10\text{V}$ , $I_D=1\text{mA}$                              | -    | 1.7  | 2.2       | V                |
| $BV_{DSS}$   | Drain-Source Breakdown Voltage    | $V_{GS}=0\text{V}$                                                  | 650  | -    | -         | V                |
| $I_{DSS}$    | Drain-Source Leakage Current      | $V_{DS}=650\text{V}$ , $V_{GS}=0\text{V}$ , $T_J=25^\circ\text{C}$  | -    | 2.5  | 30        | $\mu\text{A}$    |
|              |                                   | $V_{DS}=650\text{V}$ , $V_{GS}=0\text{V}$ , $T_J=150^\circ\text{C}$ | -    | 10   | -         |                  |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS}=6\text{V}$ , $I_D=5\text{A}$ , $T_J=25^\circ\text{C}$       | -    | 150  | 185       | $\text{m}\Omega$ |
|              |                                   | $V_{GS}=6\text{V}$ , $I_D=5\text{A}$ , $T_J=150^\circ\text{C}$      | -    | 302  | -         |                  |
| $I_{GSS}$    | Gate-Source Leakage Current       | $V_{GS}=\pm 20\text{V}$                                             | -    | -    | $\pm 100$ | nA               |

#### AC Electrical Characteristics, ( $T_J=25^\circ\text{C}$ unless otherwise specified)

| Symbol       | Parameter                    | Test Conditions                                                                                    | Min. | Typ. | Max. | Units       |
|--------------|------------------------------|----------------------------------------------------------------------------------------------------|------|------|------|-------------|
| $C_{ISS}$    | Input Capacitance            | $V_{GS}=0\text{V}$ , $V_{DS}=400\text{V}$ ,<br>$f=100\text{kHz}$                                   | -    | 505  | -    | $\text{pF}$ |
| $C_{OSS}$    | Output Capacitance           |                                                                                                    | -    | 29   | -    |             |
| $C_{RSS}$    | Reverse Transfer Capacitance |                                                                                                    | -    | 1    | -    |             |
| $Q_g$        | Total Gate Charge            | $V_{DS}=400\text{V}$ , $V_{GS}=0$ to<br>$10\text{V}$ , $I_{DS}=5\text{A}$                          | -    | 10   | -    | $\text{nC}$ |
| $Q_{GS}$     | Gate-Source Charge           |                                                                                                    | -    | 4.3  | -    |             |
| $Q_{OSS}$    | Output Charge                | $V_{GS}=0\text{V}$ , $V_{DS}=0\sim 400\text{V}$                                                    | -    | 36   | -    |             |
| $Q_{RR}$     | Reverse Recovery Charge      | $I_S=5\text{V}$ , $V_{DS}=0\text{V}$                                                               | -    | 46   | -    |             |
| $t_{d(on)}$  | Turn-On Delay Time           | $V_{DD}=400\text{V}$ , $V_{GS}=0$ to $10\text{V}$ ,<br>$I_{DS}=2\text{A}$ , $R_{G(on)}=25\Omega$ , | -    | 9    | -    | $\text{ns}$ |
| $t_{d(off)}$ | Turn-Off Delay Time          |                                                                                                    | -    | 20   | -    |             |

- Typical Electrical Characteristics

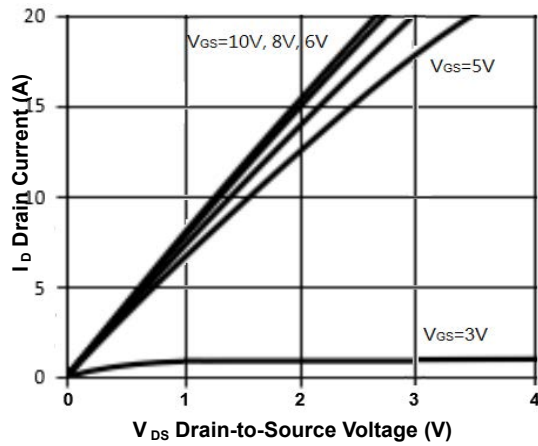


FIG.1-Output Characteristics  $T_J=25^{\circ}\text{C}$

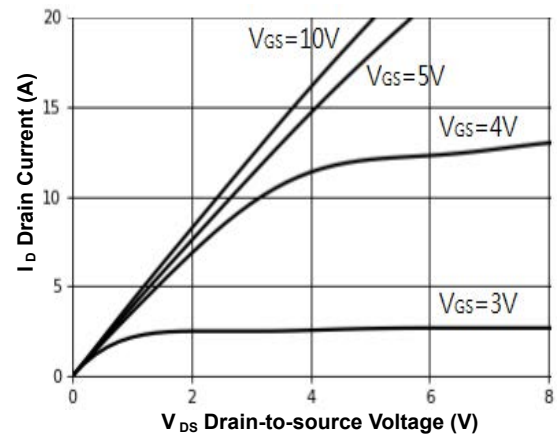


FIG.2- Output Characteristics  $T_J=150^{\circ}\text{C}$

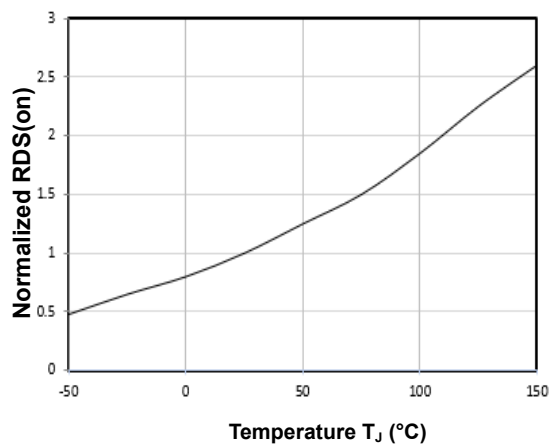


FIG.3- Normalized  $R_{DS(on)}$  vs. Temperature

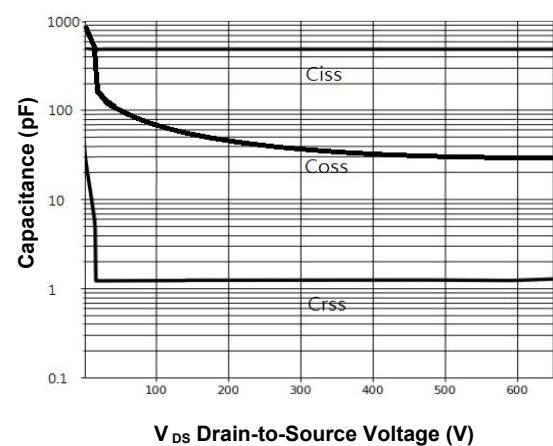


FIG.4- Capacitance vs Drain-Source Voltage

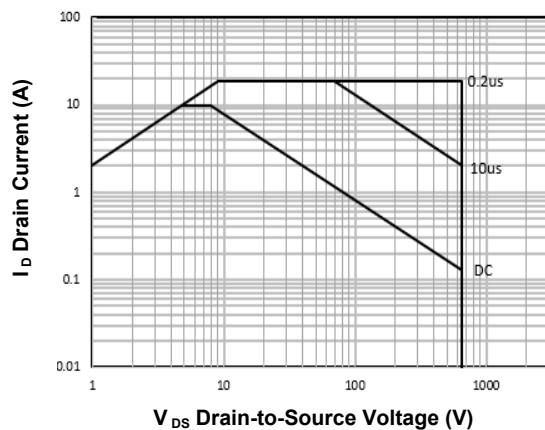


FIG.5- Safe Operating Area

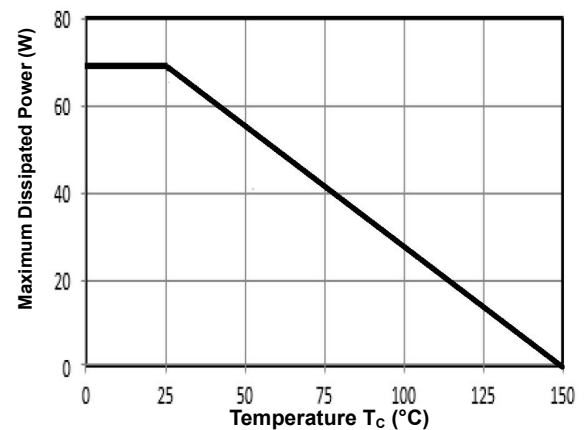


FIG.6- Maximum Power Dissipation Derating vs Case Temperature

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- Typical Electrical Characteristics

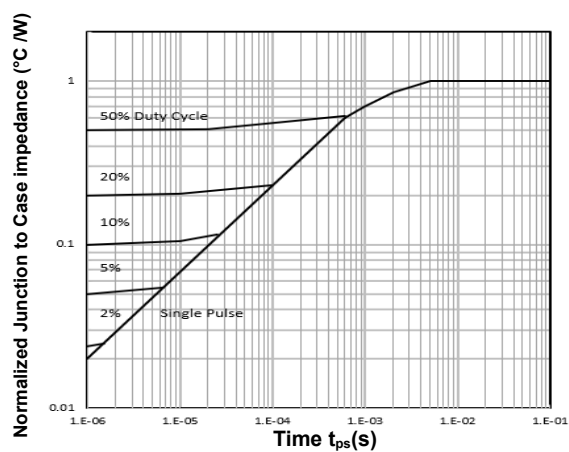


FIG.7- Transient Thermal impedance (Junction to Case)

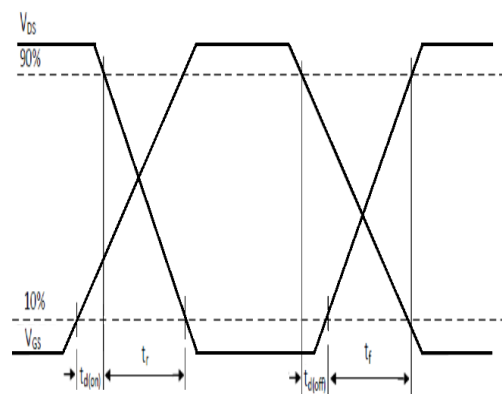
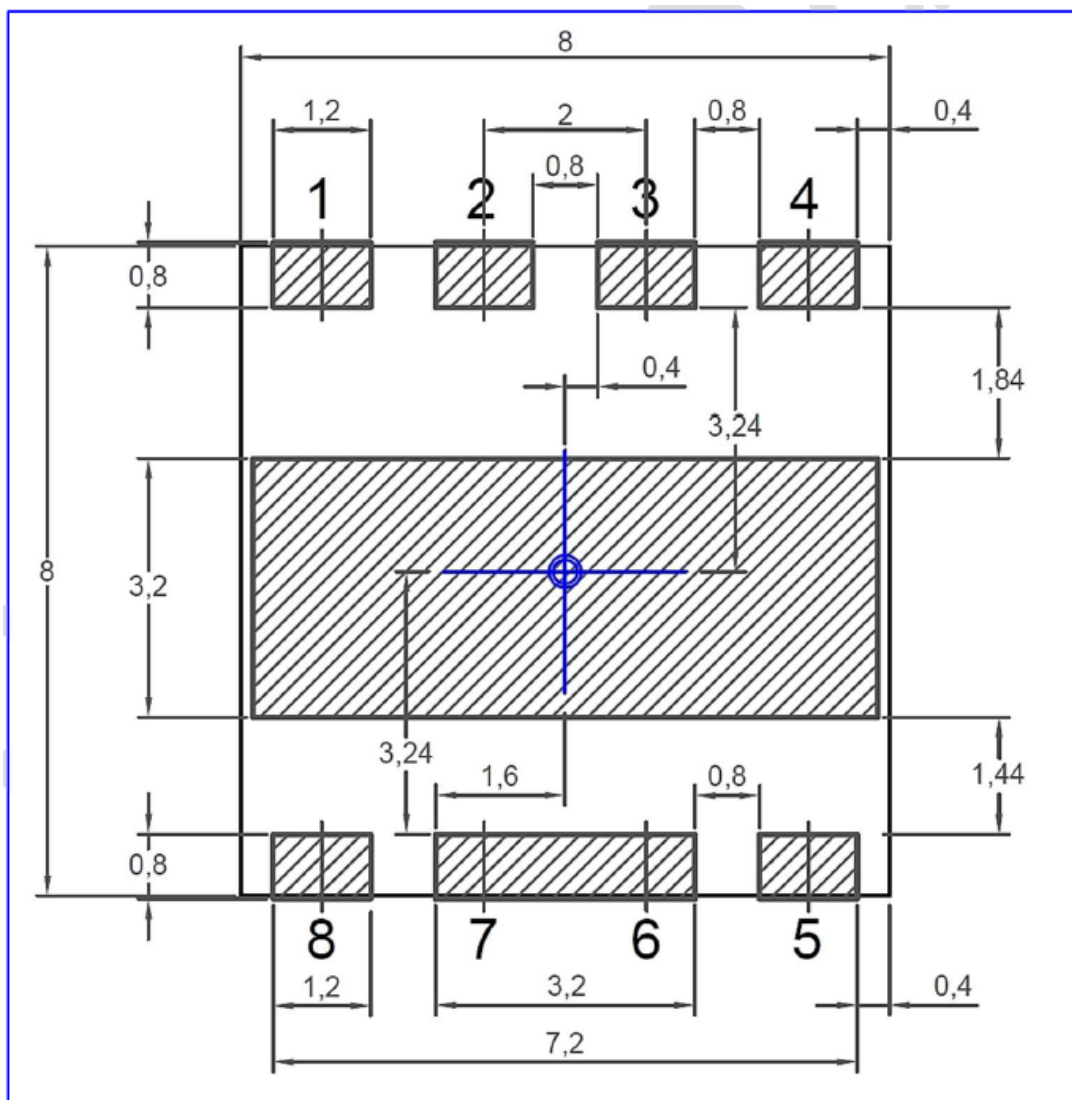


FIG.8- Switching Time Waveforms

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DFN-8X8 Recommended PCB Soldering Footprint



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